

**GaAs-IR-Lumineszenzdiode (950 nm) in SMR<sup>®</sup> Gehäuse**  
**GaAs Infrared Emitters (950 nm) in SMR<sup>®</sup> Package**  
**Lead (Pb) Free Product - RoHS Compliant**

**SFH 4510**  
**SFH 4515**



SFH 4510



SFH 4515

**Wesentliche Merkmale**

- GaAs-LED mit sehr hohem Wirkungsgrad
- SMR<sup>®</sup> (Surface Mount Radial) Gehäuse
- Für Oberflächenmontage geeignet
- Gegurtet lieferbar
- Gehäusegleich mit Fotodiode SFH 2500/ SFH 2505
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger

**Anwendungen**

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken
- Diskrete Optokoppler

**Features**

- Very highly efficient GaAs-LED
- SMR<sup>®</sup> (Surface Mount Radial) package
- Suitable for surface mounting (SMT)
- Available on tape and reel
- Same package as photodiode SFH 2500/ SFH 2505
- High reliability
- Spectral match with silicon photodetectors

**Applications**

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters
- Discrete optocouplers

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 4510	Q65110A2630	5-mm-SMR <sup>®</sup> -Gehäuse (T 1 3/4), schwarzes Epoxy-Gießharz, Anschlüsse (SFH 4510 gebogen, SFH 4515 gerade) im 2.54-mm-Raster (1/10"), Kathodenkennzeichnung: siehe Maßzeichnung. 5 mm SMR <sup>®</sup> package (T 1 3/4), black-colored epoxy resin, solder tabs (SFH 4510 bent, SFH 4515 straight) lead spacing 2.54 mm (1/10"), cathode marking: see package outline.
SFH 4515	Q65110A2633	

**Grenzwerte** ( $T_A = 25\text{ °C}$ )**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	5	V
Durchlassstrom Forward current	$I_F$ (DC)	100	mA
Stoßstrom, $t_p = 10\ \mu\text{s}$ , $D = 0$ Surge current	$I_{FSM}$	3	A
Verlustleistung Power dissipation	$P_{tot}$	150	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je $20\ \text{mm}^2$ Thermal resistance junction - ambient mounted on PC-board (FR4), padsizes $20\ \text{mm}^2$ each	$R_{thJA}$	300	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\ \text{mA}$	$\lambda_{peak}$	950	nm
Spektrale Bandbreite bei 50% von $I_{max}$ Spectral bandwidth at 50% of $I_{max}$ $I_F = 100\ \text{mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 14$	Grad deg.
Aktive Chipfläche Active chip area	$A$	0.09	$\text{mm}^2$
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	$0.3 \times 0.3$	$\text{mm}^2$
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\ \text{mA}$ , $R_L = 50\ \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 100\ \text{mA}$ , $R_L = 50\ \Omega$	$t_r, t_f$	0.5	$\mu\text{s}$

**Kennwerte** ( $T_A = 25\text{ °C}$ )  
**Characteristics** (cont'd)

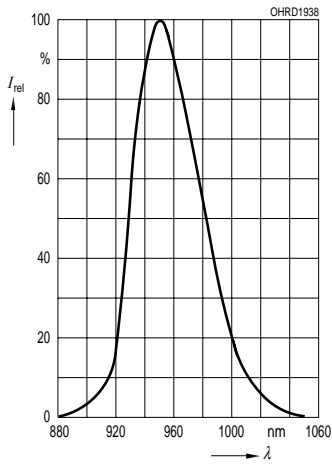
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität Capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	$C_o$	25	pF
Durchlassspannung Forward voltage $I_F = 100\text{ mA}, t_p = 20\text{ ms}$ $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	$V_F$ $V_F$	1.30 ( $\leq 1.5$ ) 2.30 ( $\leq 2.8$ )	V V
Sperrstrom Reverse current $V_R = 5\text{ V}$	$I_R$	0.01 ( $\leq 1$ )	$\mu\text{A}$
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}, t_p = 20\text{ ms}$	$\Phi_e$	22	mW
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ , $I_F = 100\text{ mA}$ Temperature coefficient of $I_e$ or $\Phi_e$ , $I_F = 100\text{ mA}$	$TC_I$	- 0.5	%/K
Temperaturkoeffizient von $V_F$ , $I_F = 100\text{ mA}$ Temperature coefficient of $V_F$ , $I_F = 100\text{ mA}$	$TC_V$	- 2	mV/K
Temperaturkoeffizient von $\lambda$ , $I_F = 100\text{ mA}$ Temperature coefficient of $\lambda$ , $I_F = 100\text{ mA}$	$TC_\lambda$	0.3	nm/K

**Strahlstärke  $I_e$  in Achsrichtung**gemessen bei einem Raumwinkel  $\Omega = 0.01$  sr**Radiant Intensity  $I_e$  in Axial Direction**at a solid angle of  $\Omega = 0.01$  sr

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ typ}}$ $I_{e \text{ min}}$	50 $\geq 25$	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ $\mu$ s	$I_{e \text{ typ}}$	450	mW/sr

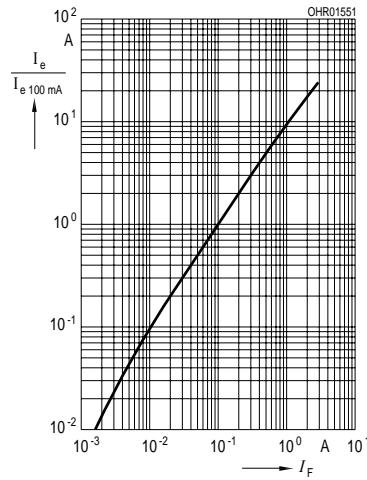
**Relative Spectral Emission**

$I_{rel} = f(\lambda)$



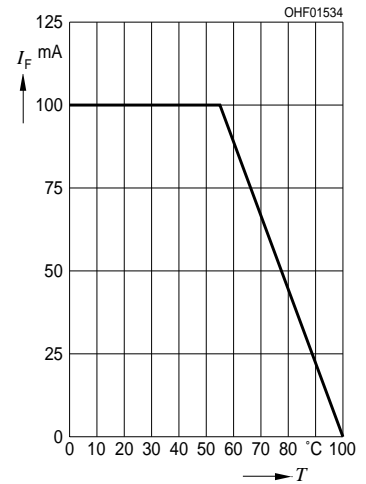
**Radiant Intensity**  $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse,  $t_p = 20 \mu\text{s}$



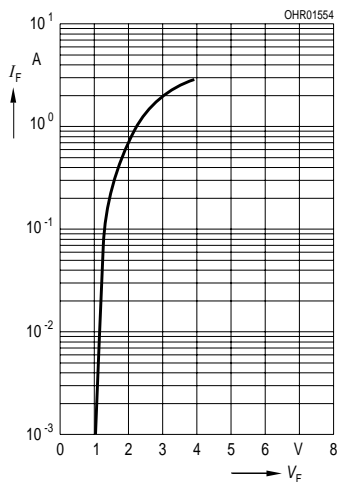
**Max. Permissible Forward Current**

$I_F = f(T_A)$



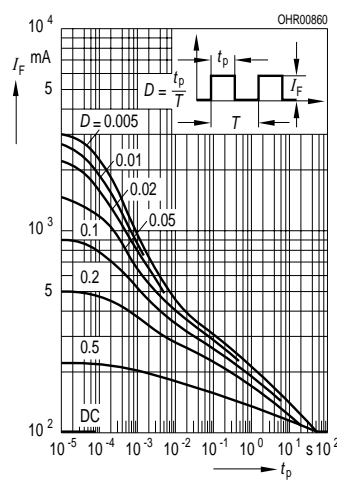
**Forward Current**

$I_F = f(V_F)$ , single pulse,  $t_p = 20 \mu\text{s}$

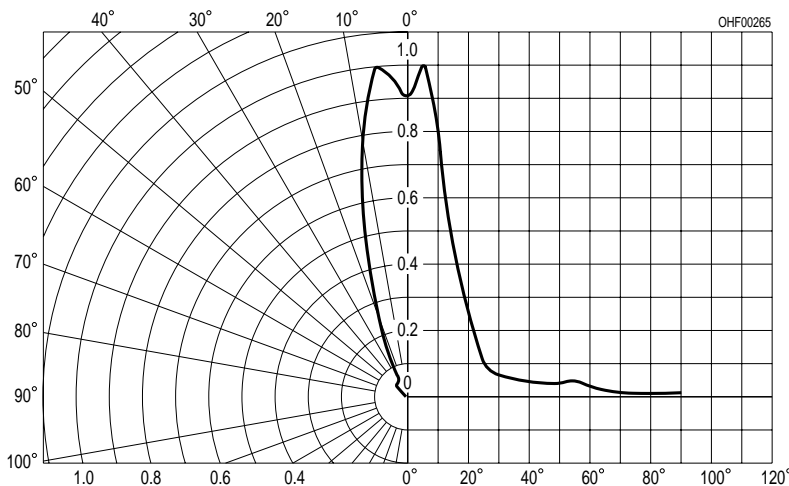


**Permissible Pulse Handling Capability**

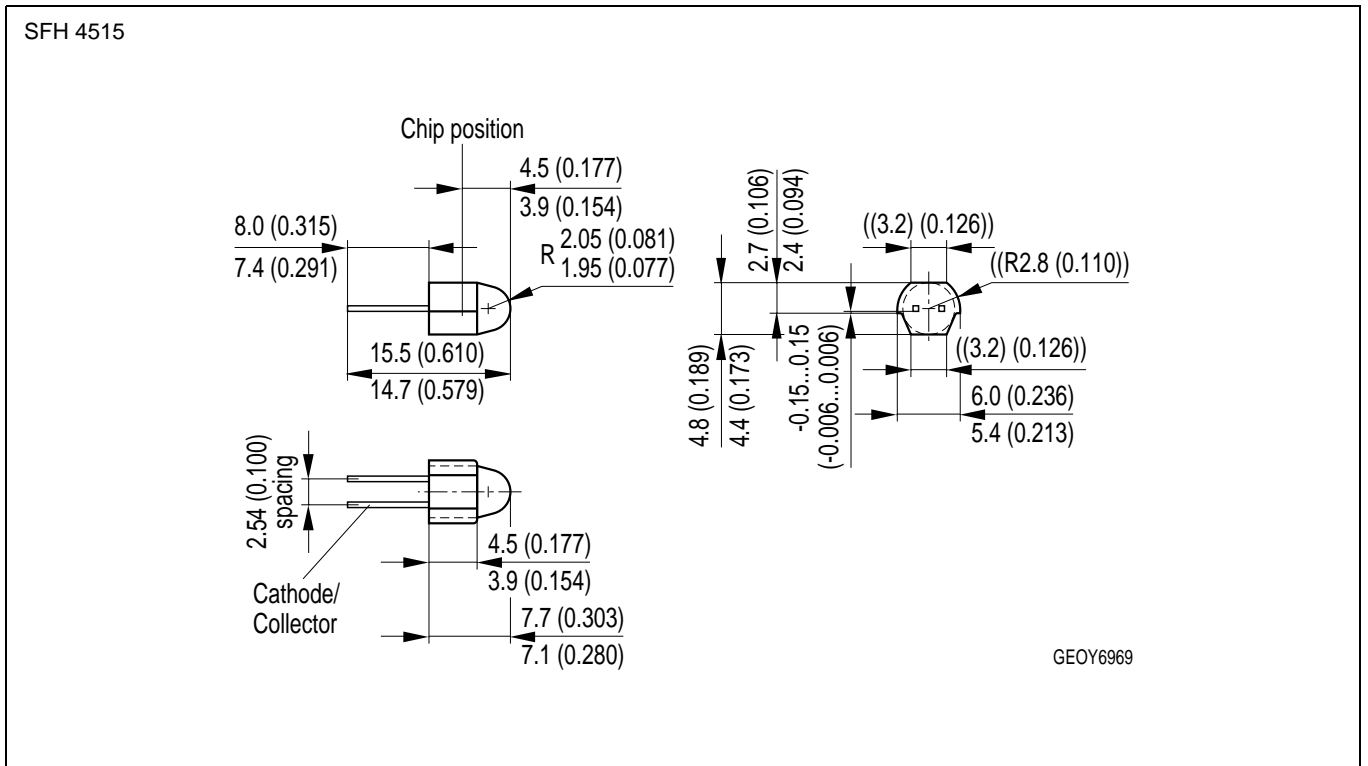
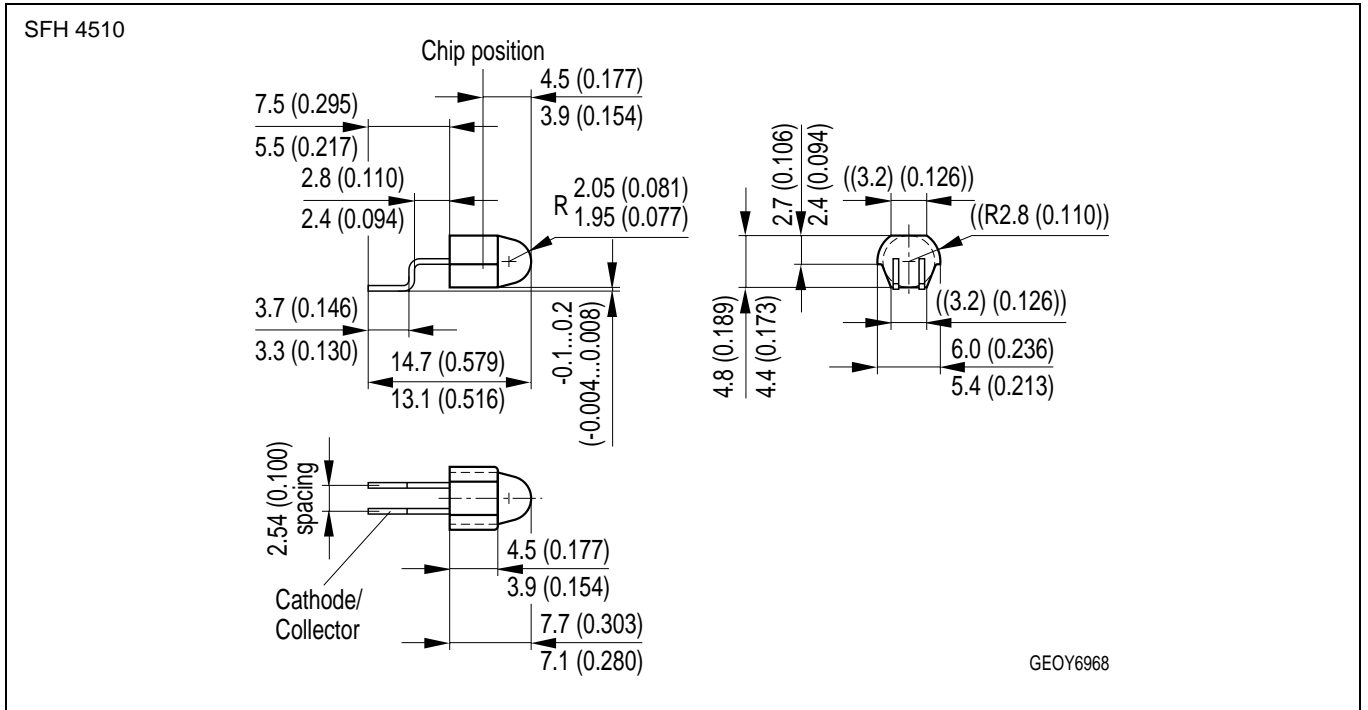
$I_F = f(\tau)$ ,  $T_A = 25 \text{ }^\circ\text{C}$ , duty cycle  $D = \text{parameter}$



**Radiation Characteristics**  $I_{rel} = f(\varphi)$

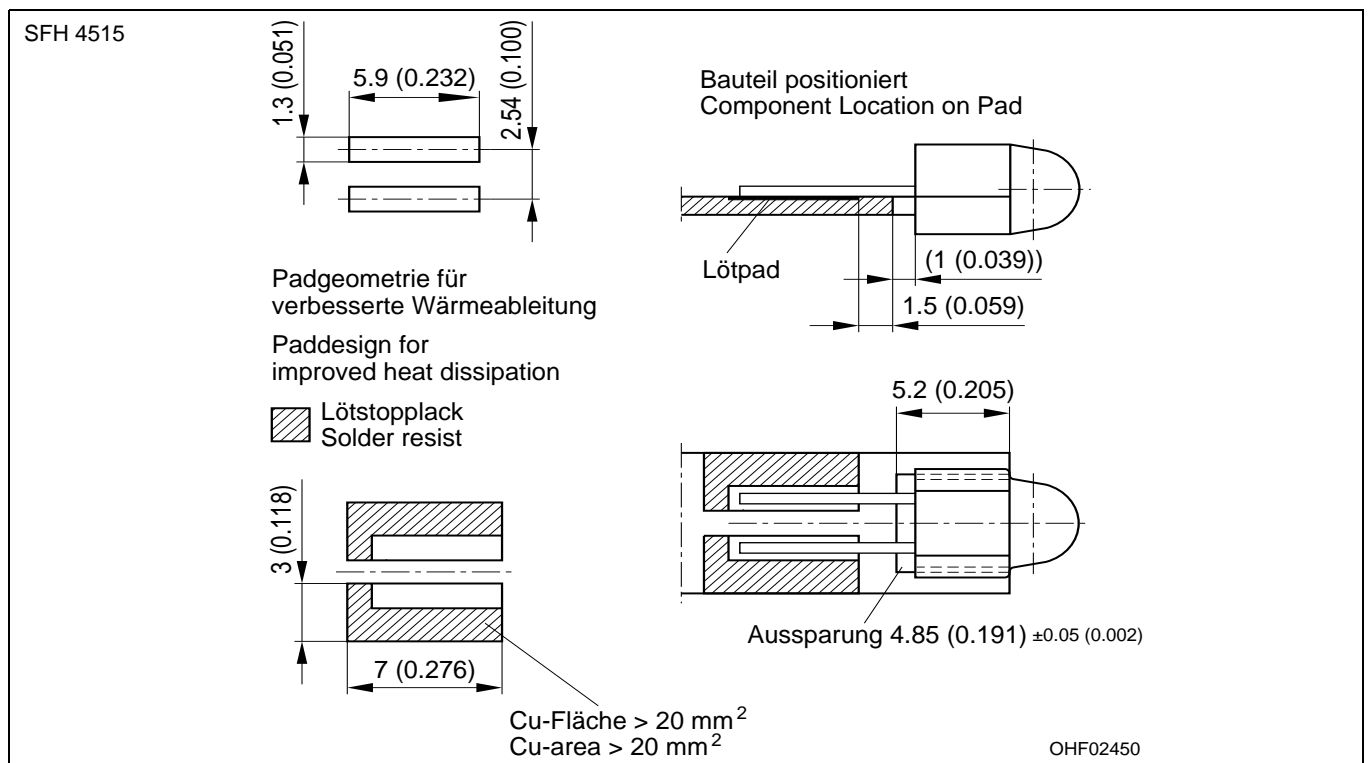
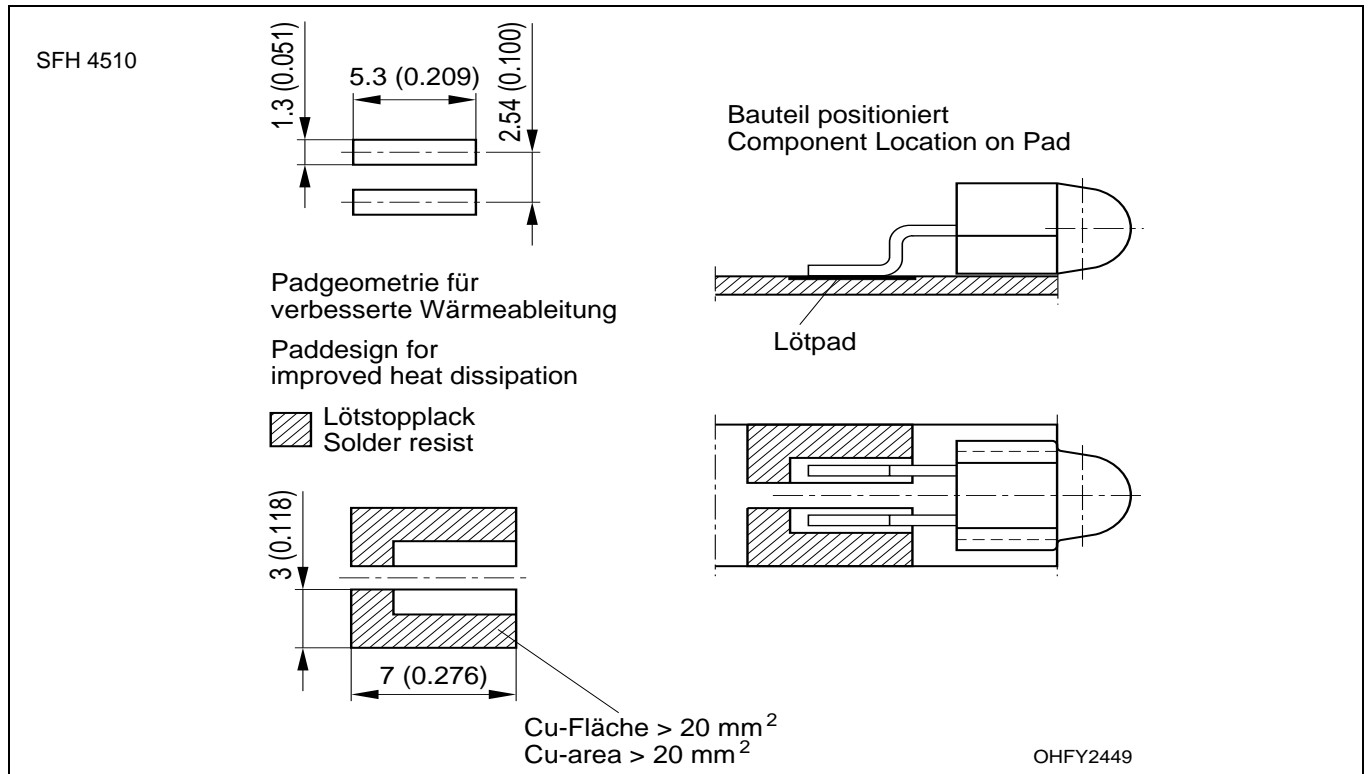


Maßzeichnung  
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

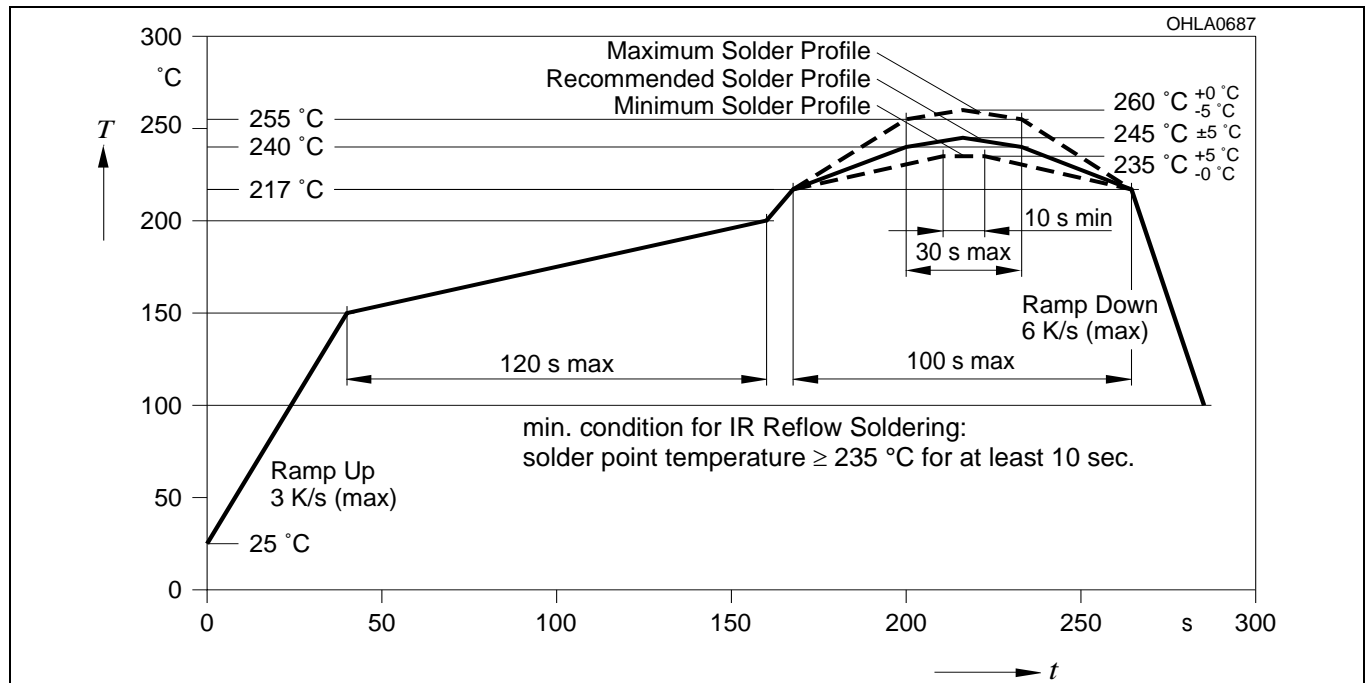
**Empfohlenes Lötpaddesign**  
**Recommended Solder Pad**



Maße in mm (inch) / Dimensions in mm (inch).

**Lötbedingungen**  
**Soldering Conditions**  
**Reflow Lötprofil für bleifreies Löten**  
**Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 3  
 Preconditioning acc. to JEDEC Level 3  
 (nach J-STD-020C)  
 (acc. to J-STD-020C)



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